

Supporting Information

Oxide Neuromorphic Transistors Gated by Polyvinyl Alcohol Solid Electrolyte with Ultralow Power Consumption

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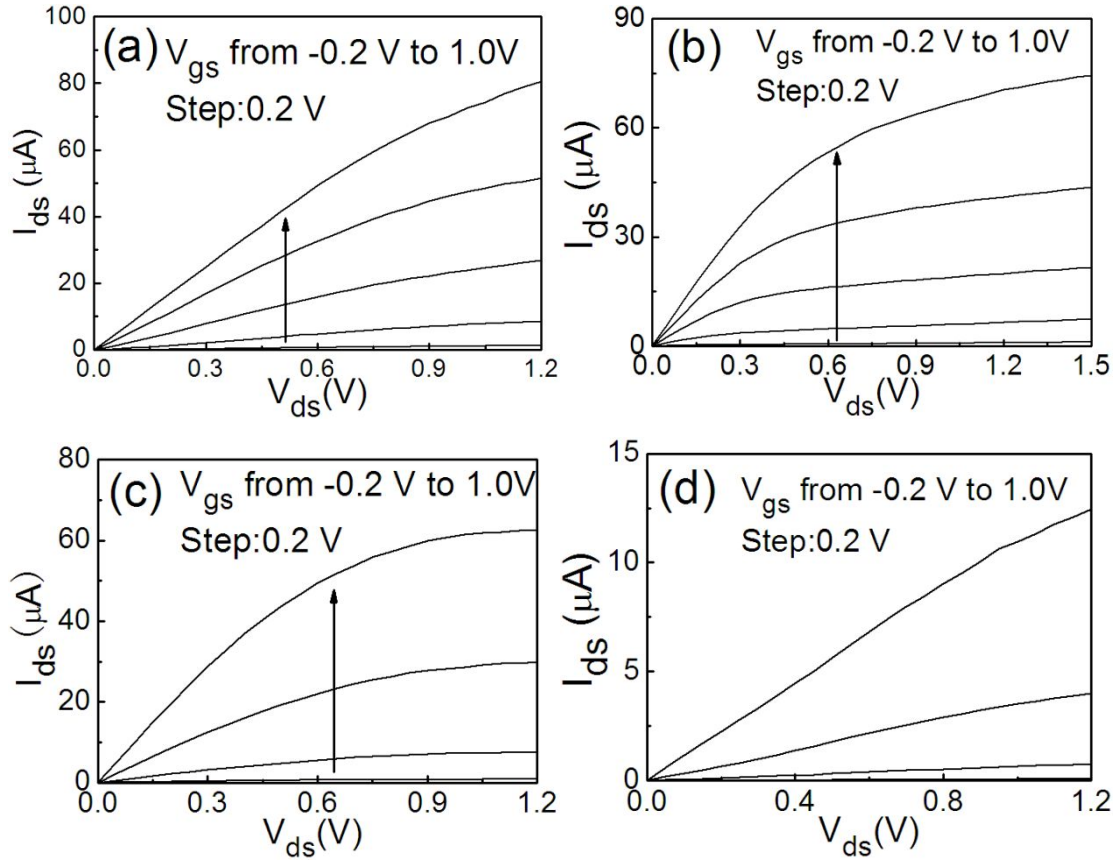


Figure S1 Output curves with different channel thickness ranged between ~ 30 nm and ~ 7 nm. (a) Channel thickness of ~ 30 nm. (b) Channel thickness of ~ 23 nm. (c) Channel thickness of ~ 16 nm. (d) Channel thickness of ~ 7 nm.

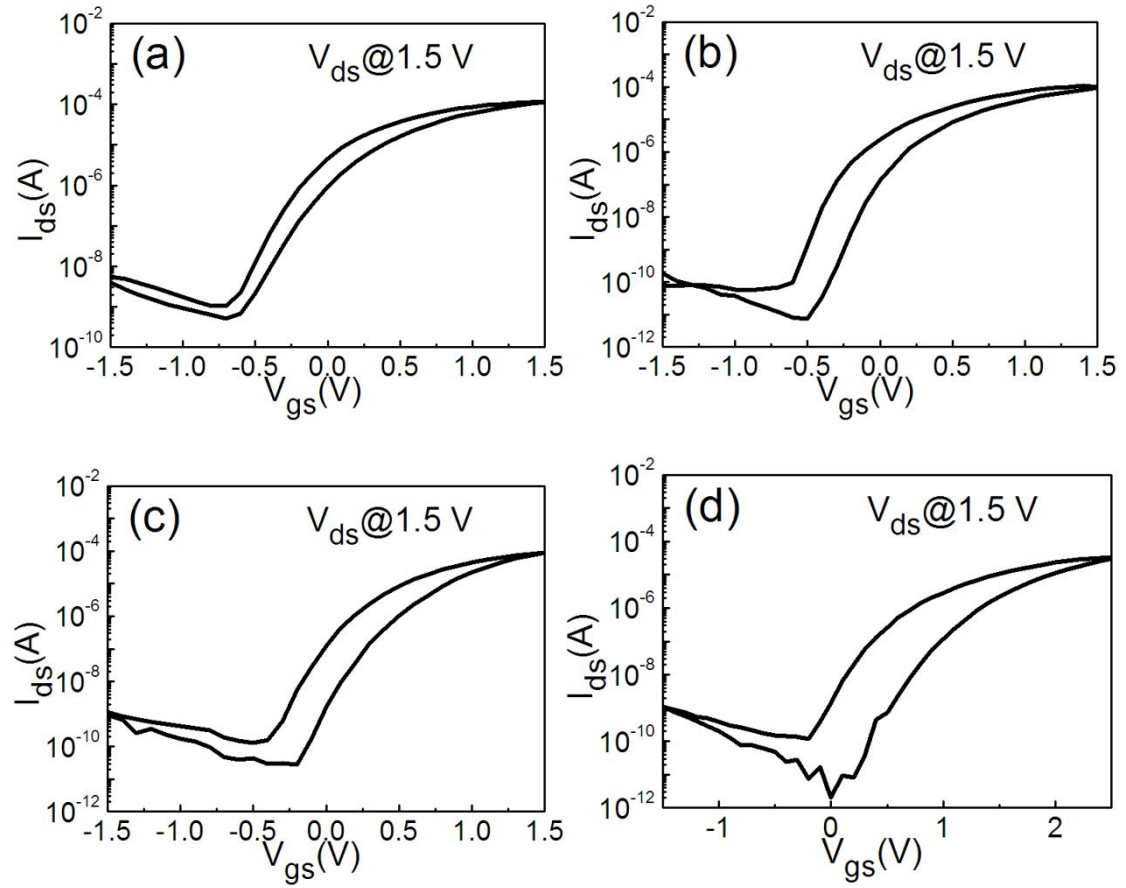


Figure S2 Transfer curves with different channel thickness ranged between ~ 30 nm and ~ 7 nm. (a) Channel thickness of ~ 30 nm. (b) Channel thickness of ~ 23 nm. (c) Channel thickness of ~ 16 nm. (d) Channel thickness of ~ 7 nm.